

**34 EDS Members Elected to the IEEE Grade of Fellow
Effective 1 January 2004**

Mark T. Bohr, Intel Corp, Hillsboro, OR, USA
for leadership in advancing CMOS logic technologies

Thomas J. Brazil, National University of Ireland, Dublin, Ireland
for contributions to circuit level modeling of non-linear devices

Kevin F. Brennan, Georgia Tech, Atlanta, GA, USA
*for contributions to the modeling of impact ionization in heterostructures
and multiquantum well structures*

**Constantin Bulucea, National Semiconductor Corp., Santa Clara, CA,
USA**
for contributions to transistor engineering in the area of power electronics

**Hsing-Yao Chen, Chunghwa Picture Tubes, LTD, Fox River Grove, IL,
USA**
for contributions to electron gun design for color cathode ray tubes

Denice Denton, University of Washington, Seattle, WA, USA
for leadership in engineering education and faculty mentoring

Robert R. Doering, Texas Instruments, Inc., Dallas, TX, USA
*for leadership in the development of sub-micron CMOS and semiconductor
manufacturing technology*

Robert H. Eklund, Texas Instruments, Inc., Plano, TX, USA
*for leadership in the development and manufacturing of sub-micron CMOS
technologies*

Hiromu Fujioka, Osaka University, Osaka, Japan
*for contributions to electron beam testing of semiconductor devices and
circuits*

Stephen M. Goodnick, Arizona State University, Tempe, AZ, USA
*for contributions to carrier transport fundamentals and semiconductor
devices*

Erik H.M. Heijne, CERN, Geneva, Switzerland
*for contributions to semiconductor detector systems and radiation tolerant
detector readout electronics*

Jerry Hudgins, University of South Carolina, Columbia, SC, USA
for contributions to the design, modeling, and teaching of semiconductor devices for power electronics

Shuji Ikeda, Trecenti Technologies, Inc., Ibaraki, Japan
for contributions to the development and manufacturing of static random access memory

Hajime Ishikawa, Fujitsu Laboratories Ltd., Kanagawa, Japan
for technical leadership in the development of high-performance Si and GaAs devices and circuits

Robert W. Jackson, University of Massachusetts, Amherst, MA, USA
for contributions to the electromagnetic modeling of microwave integrated circuits and packaging

Kenneth M. Lakin, TFR Technologies, Inc., Bend, OR, USA
for contributions to thin-film resonator technology and applications

Colin C. McAndrew, Motorola, Tempe, AZ, USA
for contributions to compact and statistical modeling of semiconductor devices

Meyya Meyyappan, NASA Ames Research Center, Moffett Field, CA, USA
for leadership in the development of nanoelectronic devices and processes

Alexander Nosich, Institute of Radio-Physics and Electronics of the National Academy of Sciences of Ukraine, Kharkov, Ukraine
for contributions to the applications of computational electromagnetics to antennas and open waveguides

Hiroshi Nozawa, Kyoto University, Kyoto Prefecture, Japan
for contributions to nonvolatile semiconductor memories

Mikael L. Ostling, KTH, Royal Institute of Technology, Kista, Sweden
for contributions to semiconductor device technology and education

Jerzy Ruzyllo, Pennsylvania State University, University Park, PA, USA
for contributions to ultrathin oxidation in microelectronic manufacturing

Victor Ryzhii, University of Aizu, Fukushima, Japan
for contributions to the development of quantum well infrared photodetectors and quantum dot infrared photodetectors

Nobuhiko Sawaki, Nagoya University, Nagoya, Japan
for contributions to the development of group III-nitride semiconductor materials and devices

Martin A. Schmidt, MIT, Reading, MA, USA
for contributions to design and fabrication of microelectromechanical systems

David B. Scott, Texas Instruments, Inc., Plano, TX, USA
for contributions to CMOS and BICMOS technology and circuits

Ninoslav Stojadinovic, University of Nis, Nis, Serbia & Montenegro
for contributions to the reliability physics of metal-oxide-semiconductor devices

Roger W. Sudbury, MIT Lincoln Laboratory, Lexington, MA, USA
for leadership in gallium arsenide integrated circuits

Christer M. Svensson, Linkoping University, Linkoping, Sweden
for contributions to single phase clocking and high speed CMOS circuits

Stuart K. Tewksbury, Stevens Institute of Technology, Hoboken, NJ, USA
for contributions to telecommunications and interconnections in high performance digital systems

Douglas P. Verret, Texas Instruments, Inc., Stafford, TX, USA
for leadership in the commercialization of bipolar and BiCMOS technologies

Dwight L. Woolard, US Army Research Lab., Research Triangle Park, NC, USA
for leadership in the discovery and development of novel sensing methodologies and advanced electronic devices at terahertz frequencies

Shin-Tson Wu, University of Central Florida, Orlando, FL, USA
for contributions to liquid crystal displays and tunable photonic devices

Katsumi Yoshino, Osaka University, Osaka, Japan
for contributions to organal electronic and optoelectronic materials

*The Nominations of the Following IEEE Members Were Evaluated by
EDS But the individuals are Not Current Members of EDS*

Gary B. Bronner, IBM, Hopewell Junction, NY, USA
for contributions to dynamic random access memory technology

**Ghavam G. Shahidi, IBM Microelectronics, Hopewell Junction, NY,
USA**
for contributions to silicon-on-insulator technology products